NEC
ELECTRON DEVICE

N-CHANNEL MOS FIELD EFFECT POWER TRANSISTOR

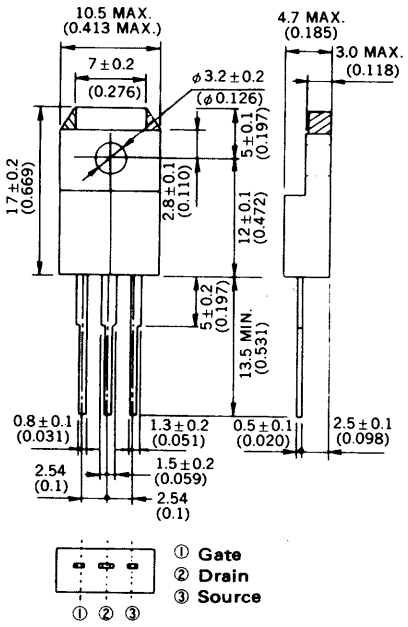
2SK1198

DESCRIPTION The 2SK1198 is N-channel MOS Field Effect Power Transistor designed for switching power supplies, AC Adapters.

FEATURES

- Suitable for switching power supplies, actuater controls, and pulse circuits.
- Low $R_{DS(on)}$
- No second breakdown
- Isolated mold package

PACKAGE DIMENSIONS
in millimeters (inches)



ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

- Storage Temperature . . . . . −55 to +150 °C
- Channel Temperature . . . . . 150 °C Maximum

Maximum Power Dissipation (T_c = 25 °C)

- Total Power Dissipation . . . . . 35 W

Maximum Voltages and Currents (T_a = 25 °C)

- V_{DSS} Drain to Source Voltage . . . . . 700 V
- V_{GSS} Gate to Source Voltage . . . . . ±20 V
- $I_{D(DC)}$ Drain Current (DC) . . . . . ±2 A
- $I_{D(pulse)}$ Drain Current (pulse)* . . . . . ±8.0 A

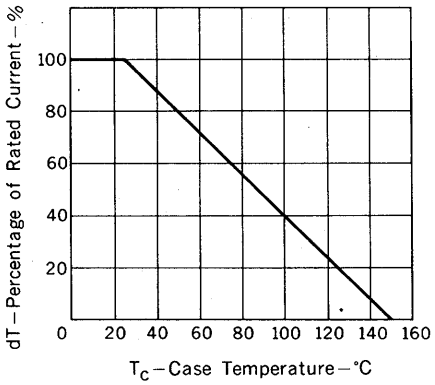
* PW ≦ 10 μs, Duty Cycle ≦ 1 %

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

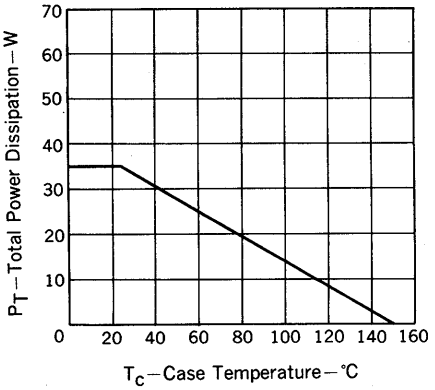
SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
I_{DSS}	Drain Leakage Current			100	μA	V_{DS} = 700 V, V_{GS} = 0
I_{GSS}	Gate to Source Leakage Current			±100	nA	V_{GS} = ±20 V V_{DS} = 0
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.5		3.5	V	V_{DS} = 10 V, I_D = 1 mA
$\|y_{fs}\|$	Forward Transfer Admittance	1.0			S	V_{DS} = 10 V, I_D = 1 A
$R_{DS(on)}$	Drain to Source On-State Resistance		2.5	3.2	Ω	V_{GS} = 10 V, I_D = 1 A
C_{iss}	Input Capacitance		950		pF	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz
C_{oss}	Output Capacitance		350		pF	
C_{rss}	Reverse Transfer Capacitance		200		pF	
$t_{d(on)}$	Turn-On Delay Time		10		ns	I_D = 1 A, V_{DD} ≒ 150 V, $V_{GS(on)}$ = 10 V, R_L = 150 Ω, R_{in} = 10 Ω
t_r	Rise Time		10		ns	
$t_{d(off)}$	Turn-Off Delay Time		60		ns	
t_f	Fall Time		20		ns	

TYPICAL CHARACTERISTICS (T_a = 25 °C)

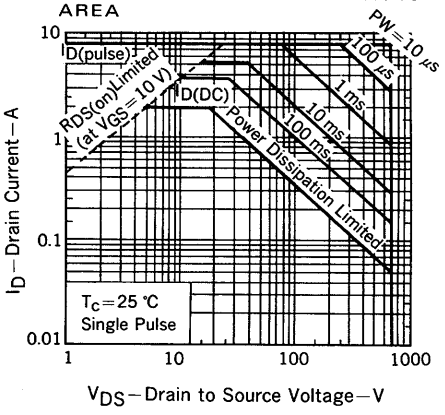
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



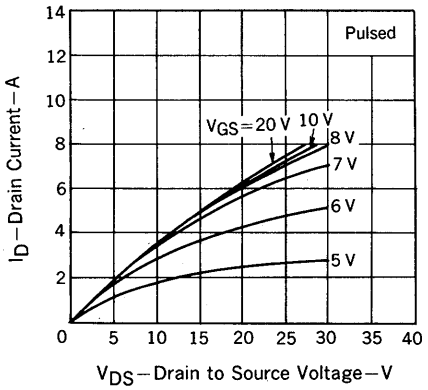
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



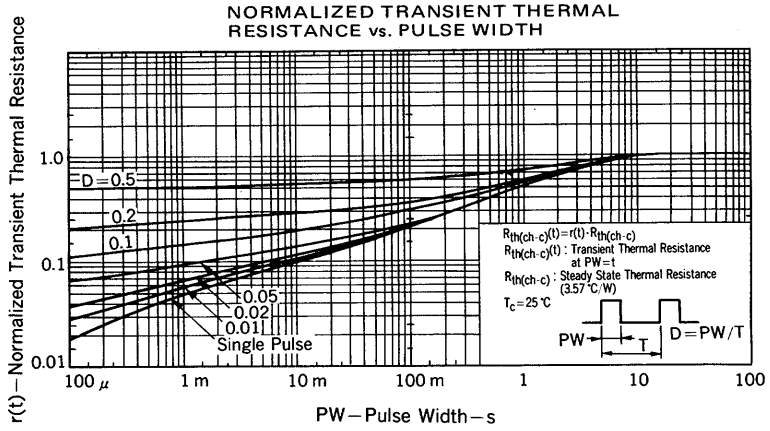
FORWARD BIAS SAFE OPERATING AREA



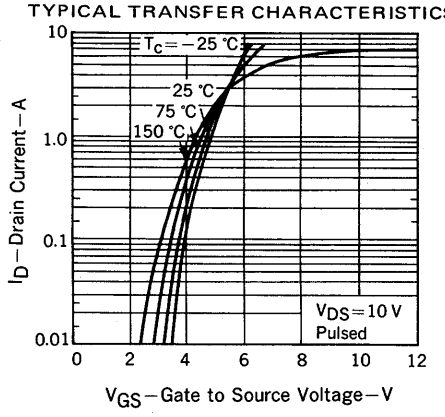
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



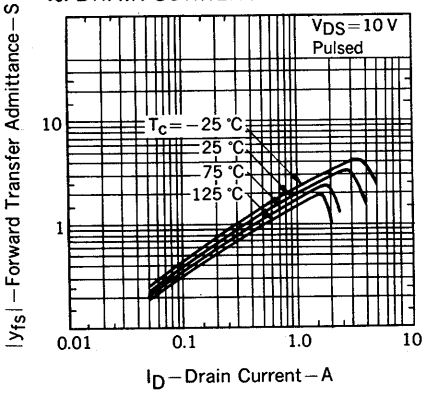
NORMALIZED TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



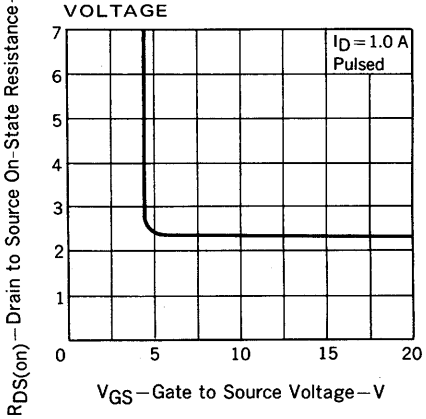
TYPICAL TRANSFER CHARACTERISTICS



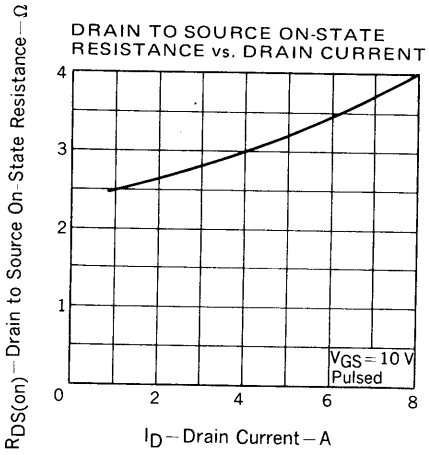
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



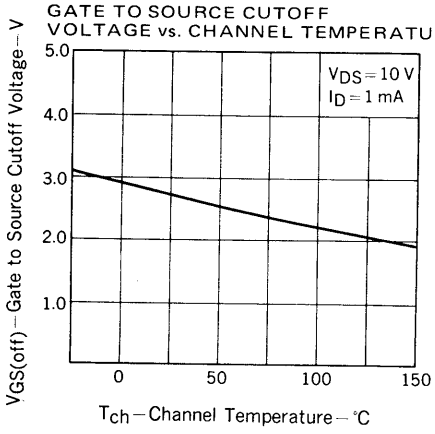
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



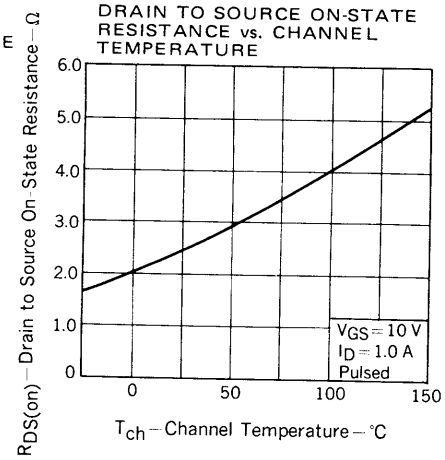
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



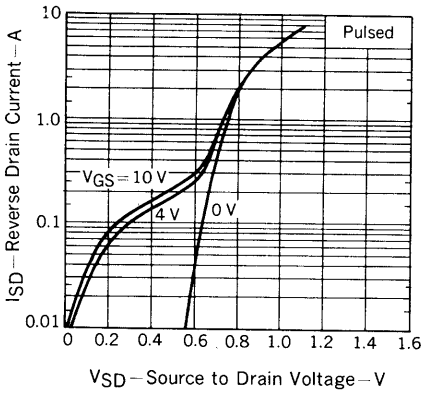
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



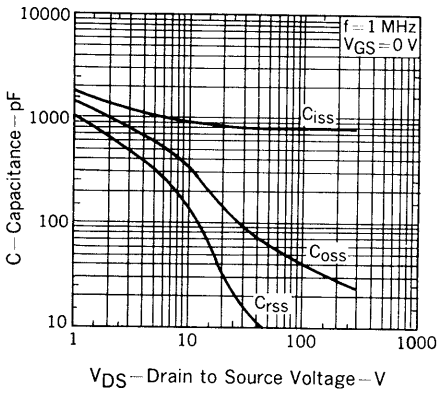
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



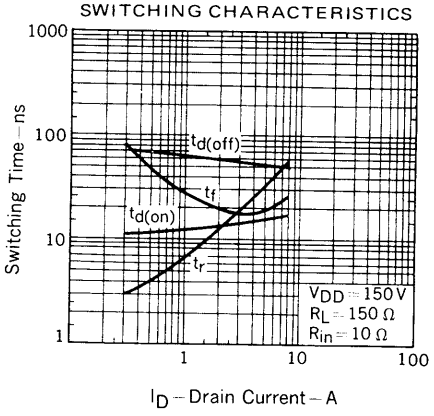
SOURCE TO DRAIN DIODE FORWARD VOLTAGE PULSED



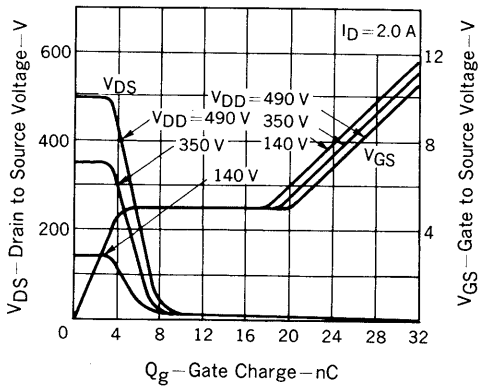
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



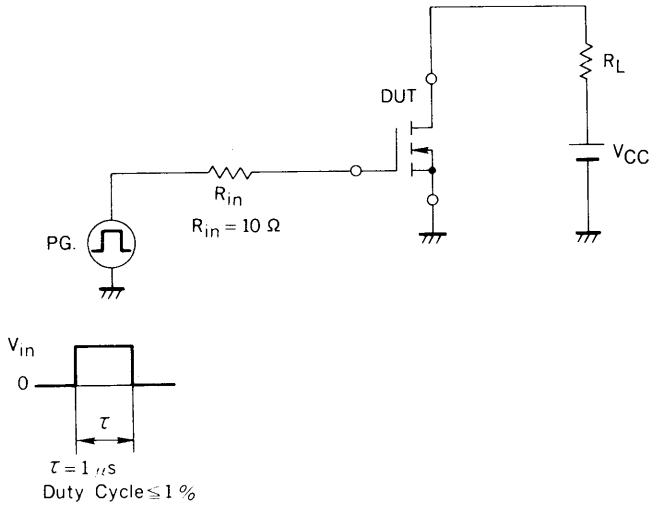
SWITCHING CHARACTERISTICS

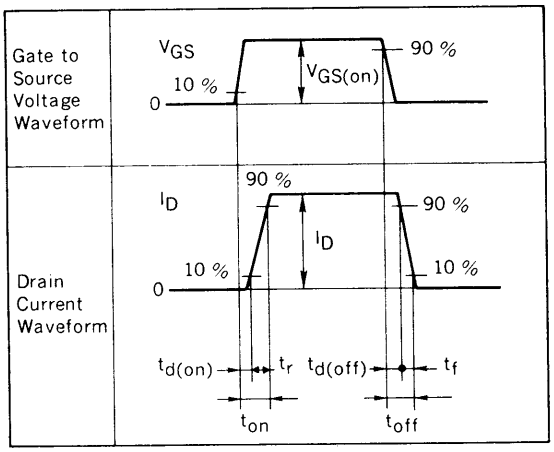


DYNAMIC INPUT CHARACTERISTICS



SWITCHING TIME TEST CIRCUIT 1





TEST CIRCUIT 2 GATE CHARGE